

DMN5L06 SINGLE N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

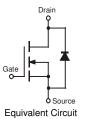
Features

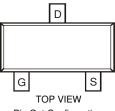
- Single N-Channel MOSFET
- Low On-Resistance
- Very Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)

Mechanical Data

- Case: SOT-23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.008 grams (approximate)







Pin Out Configuration

Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	50	V
Drain-Gate Voltage $R_{GS} \le 1.0M\Omega$		V _{DGR}	50	V
Gate-Source Voltage	Continuous Pulsed	V _{GSS}	±20 ±40	V
Drain Current (Note 1)	Continuous	I _D	280	mA
Drain Current (Note 1)	Pulsed	I _{DM}	1.5	А

SOT-23

Thermal Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 1)	Pd	350	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ ext{ heta}JA}$	357	°C/W
Operating and Storage Temperature Range	T _{j,} T _{STG}	-55 to +150	C°

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 4)							
Drain-Source Breakdown Voltage		BV _{DSS}	50		_	V	$V_{GS} = 0V, I_D = 10\mu A$
Zero Gate Voltage Drain Current	@ T _C = 25°C @ T _C = 125°C	I _{DSS}	—		0.1 500	μA	$V_{DS} = 50V, V_{GS} = 0V$
Gate-Body Leakage		I _{GSS}			±20	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage		V _{GS(th)}	0.49		1.2	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$
Static Drain-Source On-Resistance		R _{DS} (ON)		1.6 2.2	3 4	Ω	$V_{GS} = 2.7V, I_D = 0.2A,$ $V_{GS} = 1.8V, I_D = 50mA$
On-State Drain Current		I _{D(ON)}	0.5	1.0	_	Α	V _{GS} = 10V, V _{DS} = 7.5V
Forward Transconductance		g fs	200			mS	$V_{DS} = 10V, I_D = 0.2A$
Source-Drain Diode Forward Voltage		V _{SD}	0.5	_	1.4	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS							
Input Capacitance					50	pF	
Output Capacitance				_	25	pF	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz
Reverse Transfer Capacitance		C _{oss} C _{rss}		_	5.0	рF	

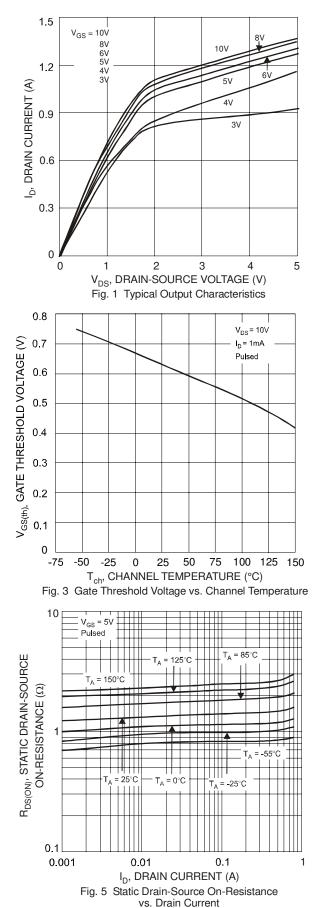
1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can Notes: be found on our website at http://www.diodes.com/datasheets/ap02001.pdf. 2.

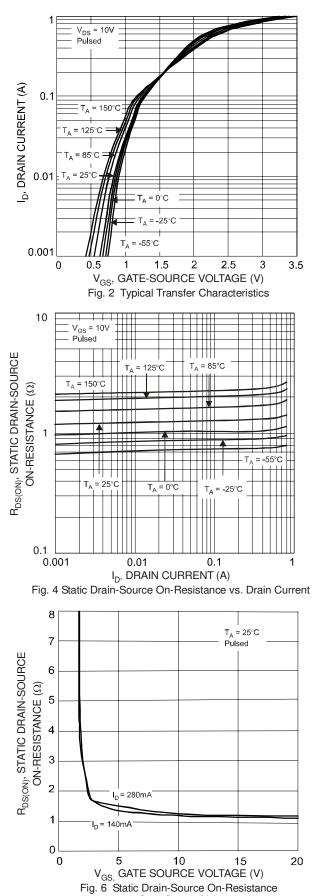
No purposefully added lead.

Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php 3.

4. Short duration pulse test used to minimize self-heating effect.

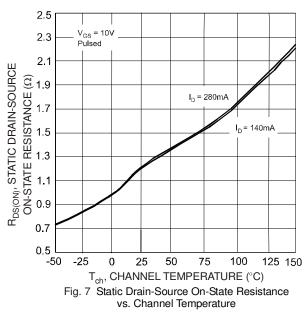


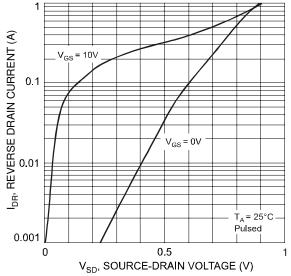


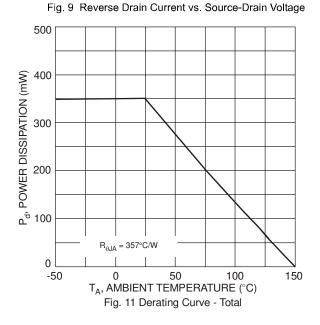


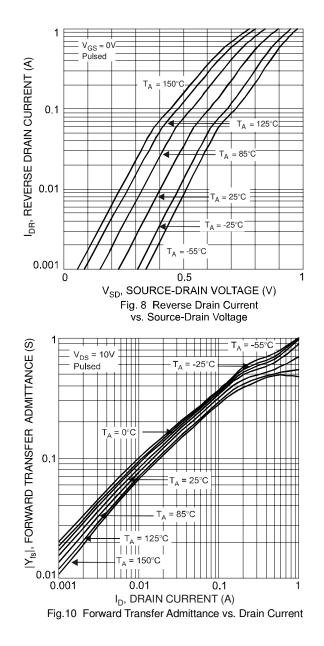
DMN5L06 Document number: DS30614 Rev. 4 - 2











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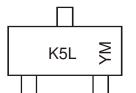


Ordering Information (Note 5)

Part Number	Case	Packaging
DMN5L06-7	SOT-23	3000/Tape & Reel

Notes: 5. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

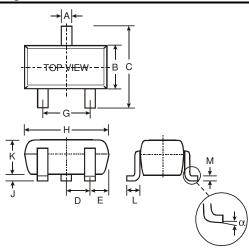


 $\begin{array}{l} \mathsf{K5L} = \mathsf{DMN5L06} \ \mathsf{Product} \ \mathsf{Type} \ \mathsf{Marking} \ \mathsf{Code} \\ \mathsf{YM} = \mathsf{Date} \ \mathsf{Code} \ \mathsf{Marking} \\ \mathsf{Y} = \mathsf{Year} \ \mathsf{ex:} \ \mathsf{S} = 2005 \\ \mathsf{M} = \mathsf{Month} \ \mathsf{ex:} \ \mathsf{9} = \mathsf{September} \end{array}$

Date	Code	Ke

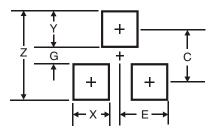
Dale Code Rey												
Year	2005		2006	2007		2008	2009		2010	2011		2012
Code	S		Т	U		V	W		Х	Y		Z
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	Ν	D

Package Outline Dimensions



SOT-23							
Dim	Dim Min Max						
Α	0.37	0.51					
В	1.20	1.40					
С	2.30	2.50					
D	0.89	1.03					
Е	0.45	0.60					
G	1.78	2.05					
н	2.80	3.00					
J	0.013	0.10					
K	0.903	1.10					
L	0.45	0.61					
М	0.085	0.180					
α	0°	8°					
All Dimensions in mm							

Suggested Pad Layout



Dimensions	Value (in mm)
Z	3.4
G	0.7
Х	0.9
Y	1.4
С	2.0
E	0.9

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